

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N5457
2N5458
2N5459

N CHANNEL FET

JEDEC TO-92 CASE (SDG)

The CENTRAL SEMICONDUCTOR 2N5457 series types are Silicon N Channel Junction FET's designed for switching and amplifier applications.

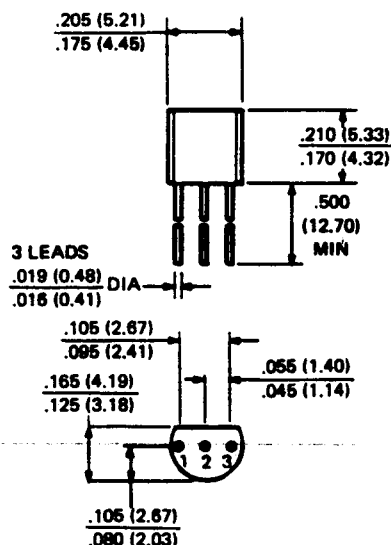
MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNIT
Drain - Source Voltage	V_{DS}	25	V
Drain - Gate Voltage	V_{DG}	25	V
Gate - Source Voltage	V_{GS}	25	V
Gate Current	I_G	10	mA
Power Dissipation	P_D	310	mW
Operating and Storage Junction Temperature	T_J, T_{STG}	-65 TO +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5457		2N5458		2N5459		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{GSS}	$V_{GS}=15\text{V}$		1.0		1.0		1.0	nA
I_{GSS}	$V_{GS}=15\text{V}, T_A=100^\circ\text{C}$		200		200		200	nA
I_{DSS}	$V_{DS}=15\text{V}$	1.0	5.0	2.0	9.0	4.0	16	mA
BV_{GSS}	$I_G=10\mu\text{A}$	25		25		25		V
$V_{GS(OFF)}$	$V_{DS}=15\text{V}$	0.5	6.0	1.0	7.0	2.0	8.0	V
C_{iss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		7.0		7.0		7.0	pF
C_{rss}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		3.0		3.0		3.0	pF
g_{fs}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{kHz}$	1000	5000	1500	5500	2000	6000	μmho
g_{os}	$V_{DS}=15\text{V}, V_{GS}=0, f=1.0\text{MHz}$		50		50		50	μmho

OUTLINE DRAWING



LEAD CODE:

1. SOURCE
2. DRAIN
3. GATE